

# UNITED STATES PATENT AND TRADEMARK OFFICE

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APPLICATION NO.	LICATION NO. FILING DATE		FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/736,230	12/15/2000		Masaaki Noda	0819-474	9138
7	590	12/13/2001			
Eric J. Robins	son		EXAMINER		
Nixon Peabody Suite 800			NGUYEN, JOSEPH H		
8180 Greensboro Drive McLean, VA 22102				ART UNIT	PAPER NUMBER
111020011, 171			2815		
			DATE MAILED: 12/13/2001		

Please find below and/or attached an Office communication concerning this application or proceeding.

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,,,,•,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	A	Application No.		Applicant(s)					
Office Autieur Oceanna		09/736,230		NODA ET AL.					
Office Action S	ummary	xaminer		Art Unit					
		loseph Nguyen		2815					
The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply									
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.  - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.  - If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.  - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.  - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).  - Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).									
Status			*						
·— ,	unication(s) filed on		·						
2a) ☐ This action is <b>FINAL</b> .	,	action is non-fir							
3) Since this application closed in accordance	3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.								
Disposition of Claims									
4)⊠ Claim(s) <u>1-12</u> is/are po	ending in the application.								
4a) Of the above claim	s) is/are withdrawn	from considera	tion.		•				
5) Claim(s) is/are allowed.									
6)⊠ Claim(s) <u>1-12</u> is/are rejected.									
7) Claim(s) is/are o	objected to.								
8) Claim(s) are subject to restriction and/or election requirement.									
Application Papers									
9) The specification is objected to by the Examiner.									
10)⊠ The drawing(s) filed on <u>15 December 2000</u> is/are: a) accepted or b)⊠ objected to by the Examiner.									
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).									
11) The proposed drawing of	correction filed on is	s: a)∐ approve	d b) disappro	ved by the Examin	er.				
If approved, corrected drawings are required in reply to this Office action.									
12) The oath or declaration is objected to by the Examiner.									
Priority under 35 U.S.C. §§ 119 and 120									
13) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).									
a)⊠ All b)⊡ Some * c)⊡ None of:									
1. Certified copies	of the priority documents h	nave been recei	ved.						
2. Certified copies	of the priority documents h	nave been recei	ved in Applicati	on No					
<ul> <li>3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).</li> <li>* See the attached detailed Office action for a list of the certified copies not received.</li> </ul>									
14) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).									
a) The translation of the foreign language provisional application has been received.									
15) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.									
Attachment(s)  1) Notice of References Cited (PTO-892)  4) Interview Summary (PTO-413) Paper No(s)									
<ol> <li>Notice of References Cited (PTO-</li> <li>Notice of Draftsperson's Patent Draftsperson's Patent Draftsperson's Patent Draftsperson's Patent Draftsperson Disclosure Statement(</li> </ol>	awing Review (PTO-948)	5) 🔲		y (PTO-413) Paper No Patent Application (PT					

U.S. Patent and Trademark Office PTO-326 (Rev. 04-01) Application/Control Number: 09/736,230

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#### **DETAILED ACTION**

## **Drawings**

Figures 14-18 should be designated by a legend such as --Prior Art-- because only that which is old is illustrated. See MPEP § 608.02(g). A proposed drawing correction or corrected drawings are required in reply to the Office action to avoid abandonment of the application. The objection to the drawings will not be held in abeyance.

## Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1-12 are rejected under 35 U.S.C. 103(a) as being unpatentable over figures 14-18 of the acknowledged prior art (APA) in view of Ronen.

Regarding claim 1, figures 14 -18 of (APA) disclose a semiconductor device with a high breakdown voltage comprising a semiconductor substrate 1 of a first conductivity type; a semiconductor region 2 of a second conductivity type which is defined in the substrate; a drain region 6 of the second conductivity type which is defined approximately at the center of the semiconductor region; a body region 4 of the first conductivity type, which is defined in the semiconductor region so as to be spaced apart from and to surround the drain region; a source region 5 of the second conductivity type which is defined in the body region; a gate insulating film 8 deposited over the body

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region; a gate electrode 10b formed on the gate insulating film; a field insulating film 3 deposited over a part of the semiconductor region, the part being located between the body and drain regions; a metal electrode 15 electrically connected to the drain region; a plurality of electrically floating gate electrodes 16,17, which are spaced apart from and surround the drain region when the device is viewed from over the substrate; and an interlevel dielectric film 9 over the gate insulating film and the field insulating film and under the plate electrodes; wherein parts of the metal electrode are extended onto the interlevel dielectric film and are located over the plate electrodes. (APA) does not disclose each said part of the metal electrodes is capacitively coupled to an associated one of the plate electrodes. However, Ronen discloses on figure 15 each part of the metal electrode 80'-1 is capacitively coupled to an associated one of the plate electrodes 80-1. In view of such teaching, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify (APA) by having each part of the metal electrode being capacitively coupled to an associated one of the plate electrode for the purpose of obtaining a higher breakdown voltage in a larger drift area as taught by Ronen (col. 10, lines 39-40).

Together, (APA) and Ronen disclose the structures of claims 2- 12.

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

US Patent 5432740 to D'Arrigo et al disclose a plurality of memory cells.

US Patent 5544103 to Lambertson discloses a nonvolatile memory device.

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US Patent 5510639 to Okuda et al disclose a non-volatile semiconductor memory cell.

US Patent 6121655 to Odanaka et al disclose the non-volatile semiconductor memory device.

#### Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Joseph Nguyen whose telephone number is (703) 308-1269. The examiner can normally be reached on Monday-Friday, 7:30 am- 4:30 pm

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Eddie Lee can be reached on (703) 308-1690. The fax phone numbers for the organization where this application or proceeding is assigned is (703) 308-7382 for regular communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

JN December 6, 2001

> SUPERVISORY PATENT EXAMINER TECHNOLOGY CENTER 2800